

100V PNP MEDIUM POWER TRANSISTOR IN SOT23

Features

- BV_{CEO} > -100V
- BV_{ECO} > -7V
- I_C = -2A Continuous Collector Current
- V_{CE(SAT)} < -130mV @ -1A
- R_{CE(SAT)} = 108mΩ Typical
- P_D = 1.25W
- High Peak Current
- Complementary Part Number ZXTN25100BFH
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

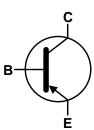
- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.008 grams (Approximate)

Applications

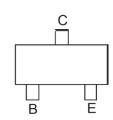
- MOSFET and IGBT Gate Driving
- DC-DC Converters
- Motor Drive
- Relay, Lamp and Solenoid Drive







Device Symbol



Top View Pin-Out

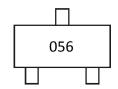
Ordering Information (Note 4)

Ī	Part Number	Marking	Reel Size (inches)	Tape Width (mm)	Quantity Per Reel
	ZXTP25100BFHTA	056	7	8	3,000

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/

Marking Information



056 = Product Type Marking Code



Absolute Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	-140	V
Collector-Emitter Voltage (Forward Blocking)	V _{CEO}	-100	V
Emitter-Collector Voltage (Reverse Blocking)	V _{ECO}	-7	V
Emitter-Base Voltage	V_{EBO}	-7	V
Continuous Collector Current (Note 5)	Ic	-2	Α
Peak Pulse Current	I _{CM}	-5	Α

Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit	
	(Note 5)		0.73 5.84		
Power Dissipation	(Note 6)	0	1.05 8.4	10/	
Linear Derating Factor	(Note 7)	P_{D}	1.25 9.6	W	
	(Note 8)		1.81 14.5		
	(Note 5)		171		
Thermal Decistores, Junction to Ambient	(Note 6)	6	119	0000	
Thermal Resistance, Junction to Ambient	(Note 7)	$R_{ heta JA}$	100	°C/W	
	(Note 8)		69		
Thermal Resistance, Junction to Lead	(Note 9)	$R_{ heta JL}$	74.95	°C/W	
Operating and Storage Temperature Range	_	T _J , T _{STG}	-55 to +150	°C	

Notes:

- 5. For a device surface mounted on 15mm x 15mm x 1.6mm FR-4 PCB with high coverage of single sided 1oz copper, in still air conditions; the device is measured when operating in a steady-state condition.
- 6. Same as note (5), except the device is surface mounted on 25mm x 25mm with 2 oz copper.
- 7. Same as note (5), except the device is surface mounted on 50mm x 50mm with 2 oz copper.
- 8. Same as note (6), except the device is measured at t<5secs.
- 9. Thermal resistance from junction to solder-point (at the end of the collector lead).

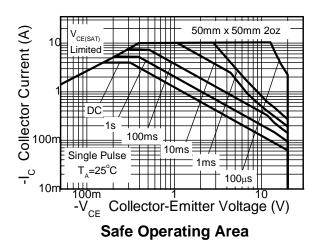
ESD Ratings (Note 10)

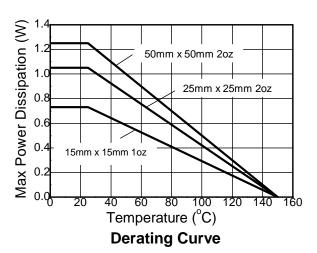
Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

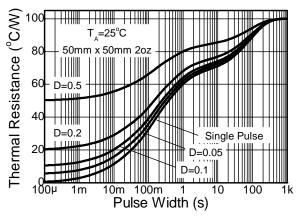
Note: 10. Refer to JEDEC specification JESD22-A114 and JESD22-A115.

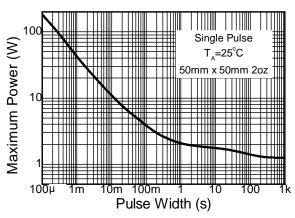


Thermal Characteristics and Derating Information









Transient Thermal Impedance

Pulse Power Dissipation



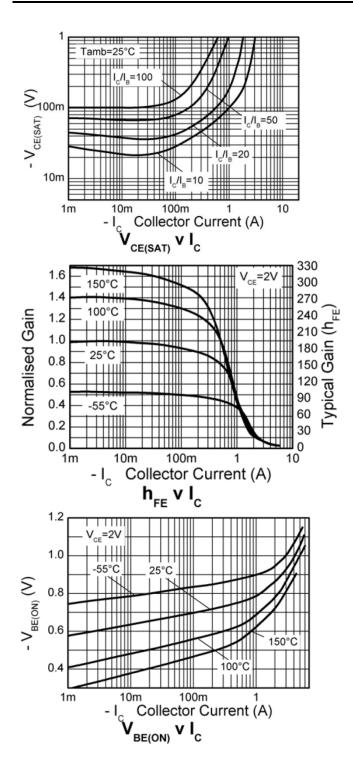
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

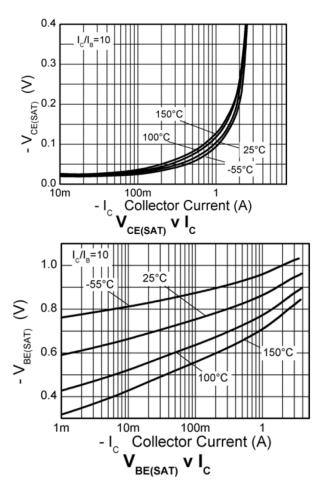
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV _{CBO}	-140	-165	_	V	$I_{C} = -100 \mu A$
Collector-Emitter Breakdown Voltage (Note 11)	BV _{CEO}	-100	-125	_	V	$I_C = -10mA$
Collector-Emitter Breakdown Voltage	BV _{CEX}	-140	-165	_	V	I_E = -100μA, R_{BC} < 1k Ω or -0.25 < V_{BE} < 1V
Emitter-Base Breakdown Voltage	BV _{EBO}	-7	-8.2	_	V	$I_E = -100 \mu A$
Collector-Base Cutoff Current	l	_	< -1	-50	nA	V _{CB} = -112V
Collector-base Cutoff Current	I _{CBO}	_		-20	μΑ	$V_{CB} = -112V, T_A = +100^{\circ}C$
Emitter-Base Cutoff Current	I _{EBO}		< -1	-50	nA	$V_{EB} = -5.6V$
		100	200	300		$I_C = -10 \text{mA}, V_{CE} = -2 \text{V}$
Static Forward Current Transfer Ratio (Note 11)	h _{FE}	55	105	_	1 1	$I_C = -1A$, $V_{CE} = -2V$
		15	25	_		$I_C = -2A$, $V_{CE} = -2V$
		_	-60	-90		$I_C = -0.5A$, $I_B = -50mA$
Collector-Emitter Saturation Voltage (Note 11)	V	_	-240	-350	mV	$I_C = -0.5A$, $I_B = -10mA$
Collector-Emitter Saturation Voltage (Note 11)	V _{CE} (SAT)	_	-100	-130	111 V	$I_C = -1A$, $I_B = -100mA$
		_	-215	-295		$I_C = -2A$, $I_B = -200mA$
Base-Emitter Saturation Voltage (Note 11)	$V_{BE(SAT)}$	_	-900	-1000	mV	$I_C = -2A$, $I_B = -200mA$
Base-Emitter Voltage (Note 11)	V _{BE(ON)}	_	-830	-950	mV	$I_C = -2A$, $V_{CE} = -2V$
Output Capacitance	Сово	_	15	25	pF	$V_{CB} = -10V$, $f = 1MHz$
Transition Frequency	f⊤	_	200	_	MHz	$V_{CE} = -5V$, $I_{C} = -100$ mA, $f = 100$ MHz
Turn-on Time	t _(ON)		31	_	ns	$V_{CC} = -10V, I_{C} = -500mA,$
Turn-off Time	t _(OFF)	_	384	_	ns	$I_{B1} = -I_{B2} = -50 \text{mA}$

Note: 11. Measured under pulsed conditions. Pulse width \leq 300 μ s. Duty cycle \leq 2%.



Typical Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)



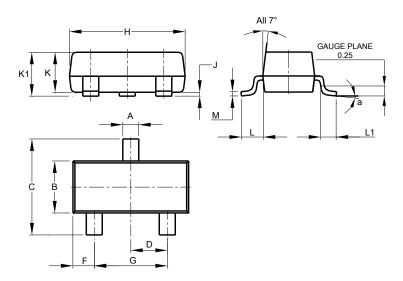




Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT23

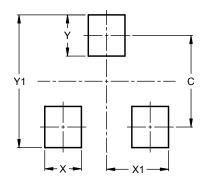


SOT23					
Dim	Min	Max	Тур		
Α	0.37	0.51	0.40		
В	1.20	1.40	1.30		
С	2.30	2.50	2.40		
D	0.89	1.03	0.915		
F	0.45	0.60	0.535		
G	1.78	2.05	1.83		
Н	2.80	3.00	2.90		
J	0.013	0.10	0.05		
K	0.890	1.00	0.975		
K1	0.903	1.10	1.025		
L	0.45	0.61	0.55		
L1	0.25	0.55	0.40		
M	0.085	0.150	0.110		
а	0°	8°			
All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT23



Dimensions	Value (in mm)		
С	2.0		
Х	0.8		
X1	1.35		
Υ	0.9		
Y1	2.9		



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